



FW217A

N-Channel Power MOSFET 35V, 6A, 39mΩ, Dual SOIC8

ON Semiconductor®

<http://onsemi.com>

Features

- On-state resistance $R_{DS(on)1}=30m\Omega$ (typ.)
- 4.5V drive
- Halogen free compliance
- Protection Diode in

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

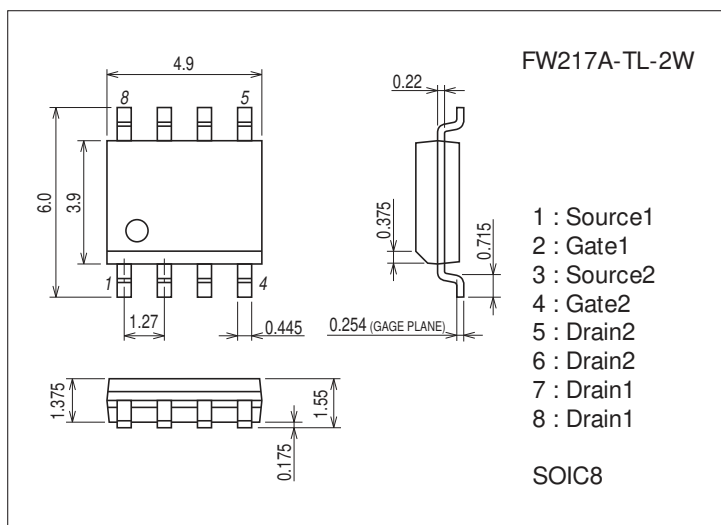
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		35	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		6	A
Drain Current ($PW \leq 10s$)	I_{DP}	Duty cycle $\leq 1\%$	6.5	A
Drain Current ($PW \leq 10\mu s$)	I_{DP}	Duty cycle $\leq 1\%$	24	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (2000mm ² ×0.8mm) 1unit, $PW \leq 10s$	1.8	W
Total Dissipation	P_T	When mounted on ceramic substrate (2000mm ² ×0.8mm), $PW \leq 10s$	2.2	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

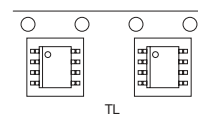
7072-001



Product & Package Information

- Package : SOIC8
- JEITA, JEDEC : SC-87, SOT-96
- Minimum Packing Quantity : 2,500 pcs./reel

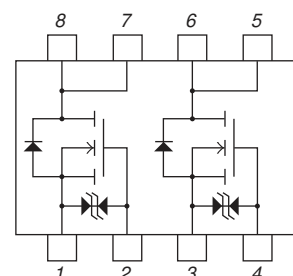
Packing Type : TL



Marking



Electrical Connection

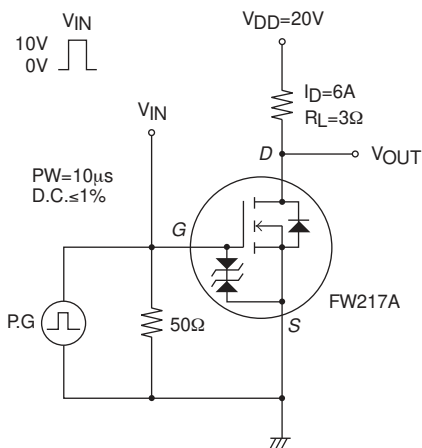


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Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	VDS=35V, VGS=0V			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.7		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=6A		3		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=6A, VGS=10V		30	39	mΩ
	RDS(on)2	ID=3A, VGS=4.5V		50	70	mΩ
Input Capacitance	Ciss	VDS=20V, f=1MHz		470		pF
Output Capacitance	Coss			70		pF
Reverse Transfer Capacitance	Crss			35		pF
Turn-ON Delay Time	td(on)			8		ns
Rise Time	tr	See specified Test Circuit.		34		ns
Turn-OFF Delay Time	td(off)			31		ns
Fall Time	tf			30		ns
Total Gate Charge	Qg			10		nC
Gate-to-Source Charge	Qgs	VDS=20V, VGS=10V, ID=6A		2		nC
Gate-to-Drain "Miller" Charge	Qgd			2		nC
Diode Forward Voltage	VSD		IS=6A, VGS=0V		0.84	1.2

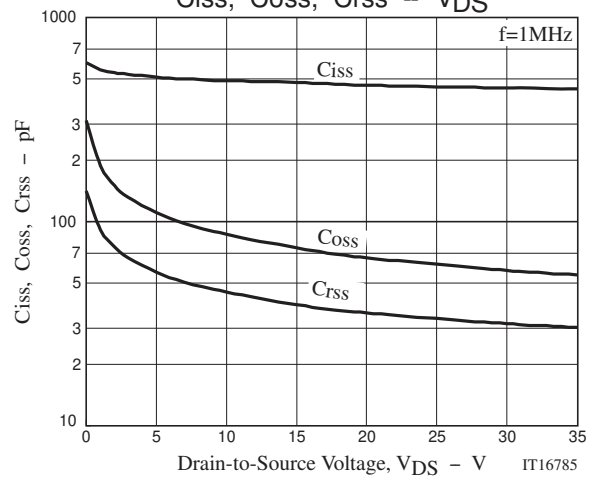
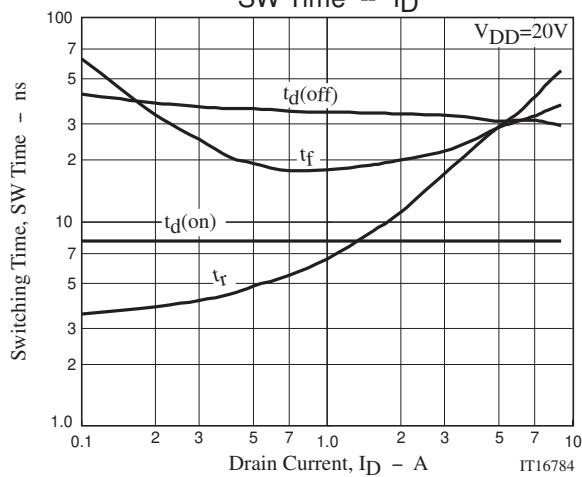
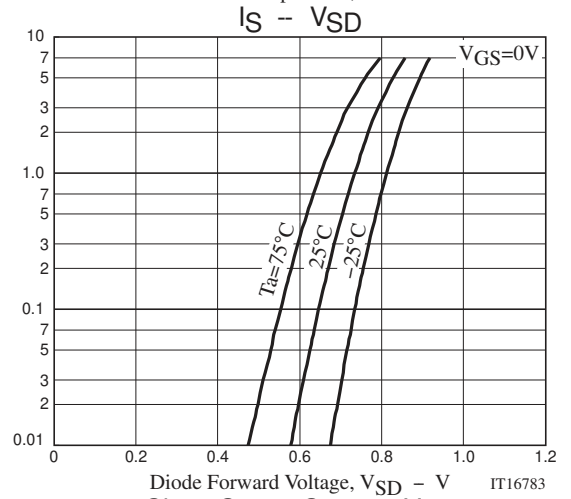
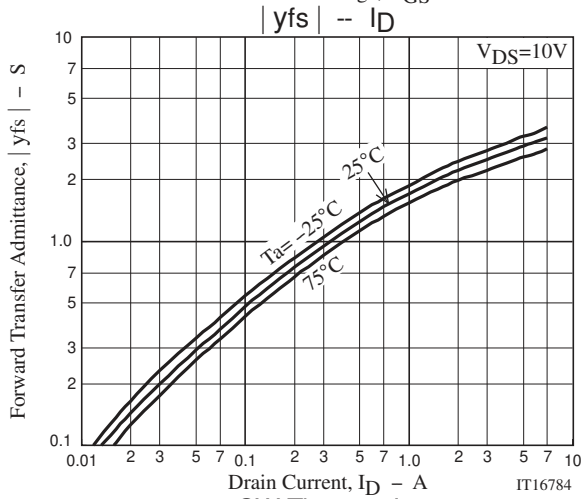
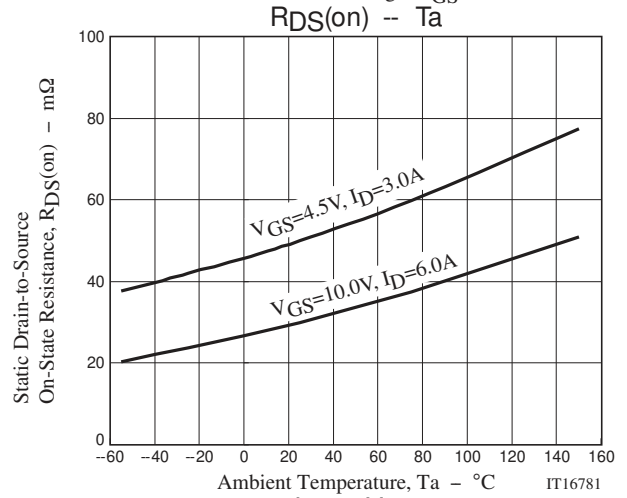
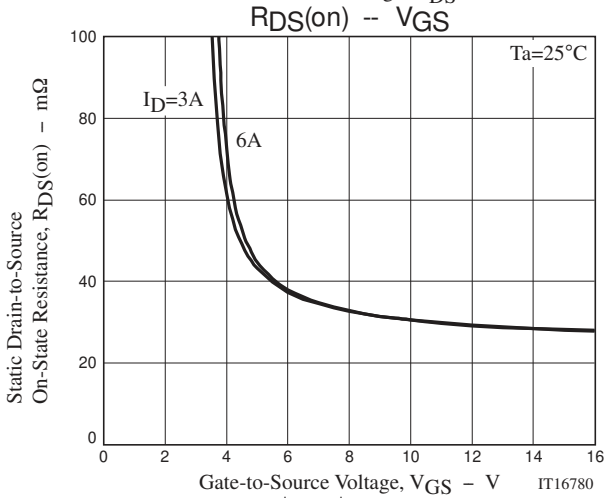
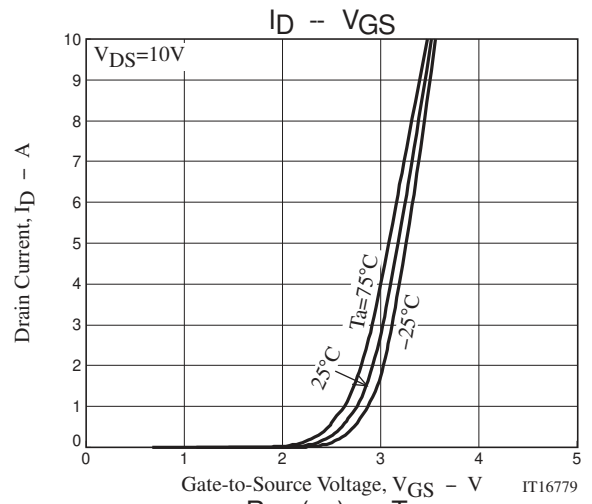
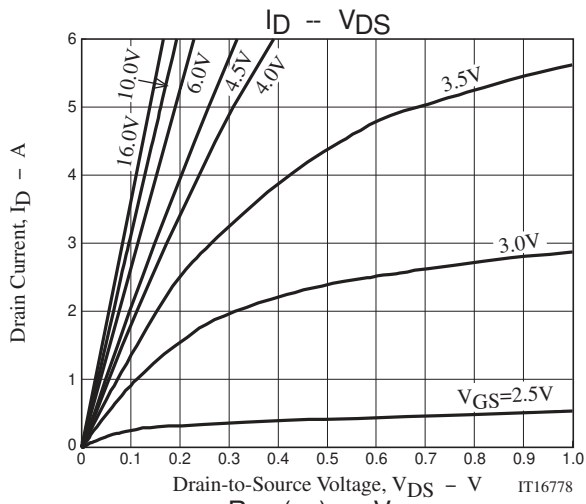
Switching Time Test Circuit

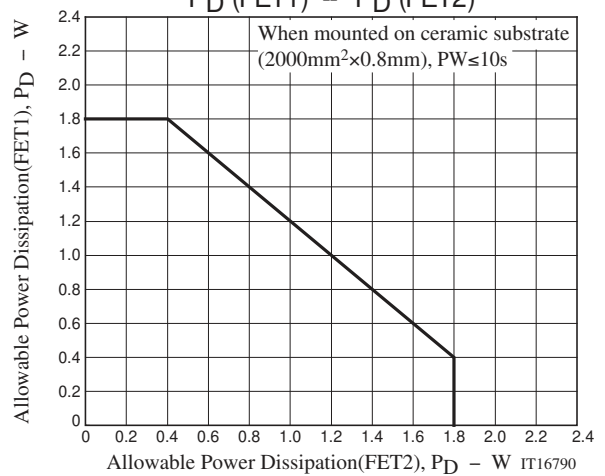
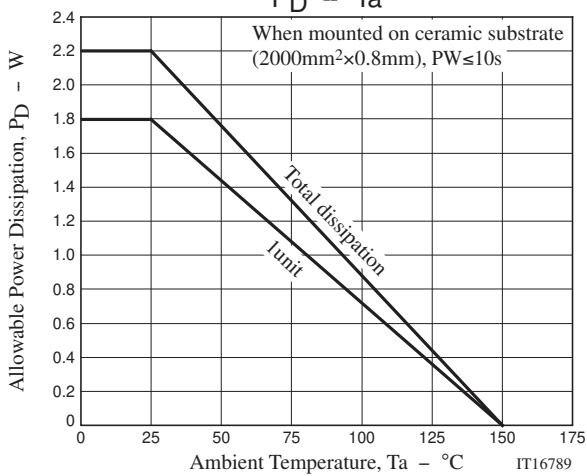
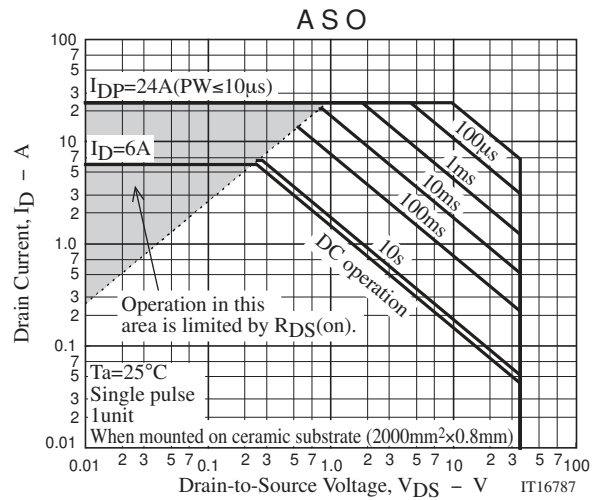
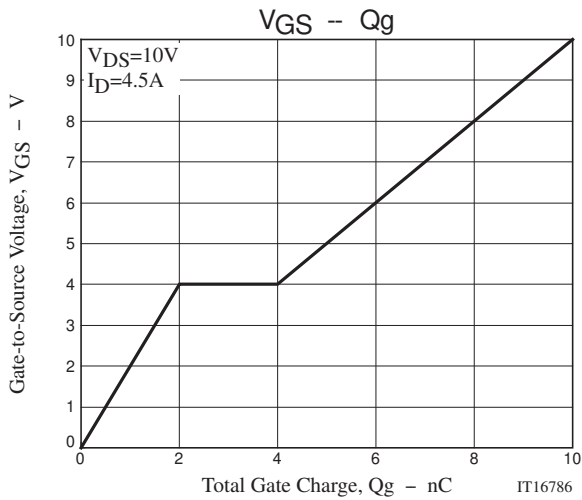


Ordering Information

Device	Package	Shipping	memo
FW217A-TL-2W	SOIC8	2,500pcs./reel	Pb Free and Halogen Free

FW217A





Taping Specification

FW217A-TL-2W

1. Packing Format

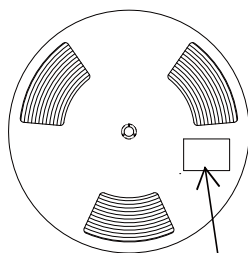
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX W206-112	Outer BOX W207-124
SOIC8	B202-101	2,500	12,500	25,000	5 reels contained Dimensions :mm(external) 340×95×340	2 inner boxes contained Dimensions :mm(external) 360×210×375

Packing method

Reel label, Inner box label (unit: mm)

Outer box label

It is a label at the time of factory shipments.
 The form of a label may change in physical distribution process.



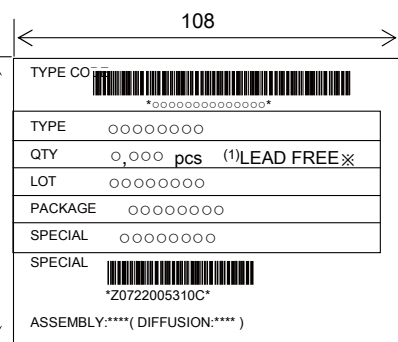
Type No. →
 LOT No. →
 Quantity →
 Origin →

Reel label



NOTE(1)

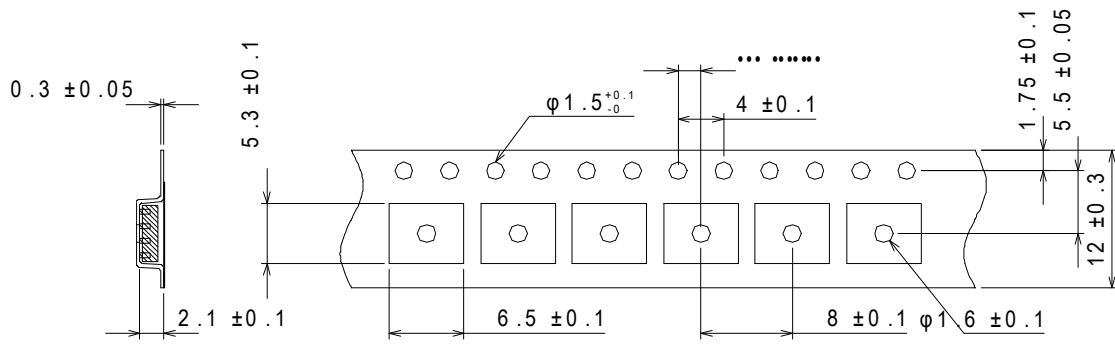
The LEAD FREE 4 description shows that it is complete lead free.



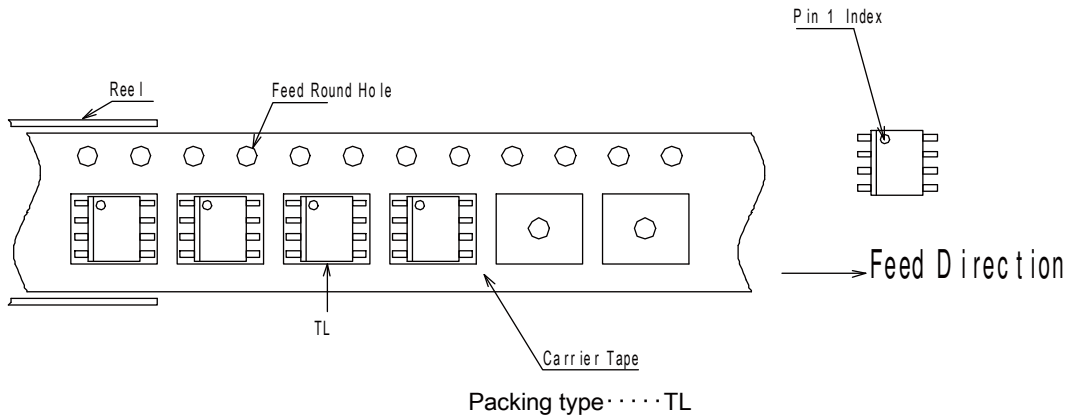
Label	JEITA Phase
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

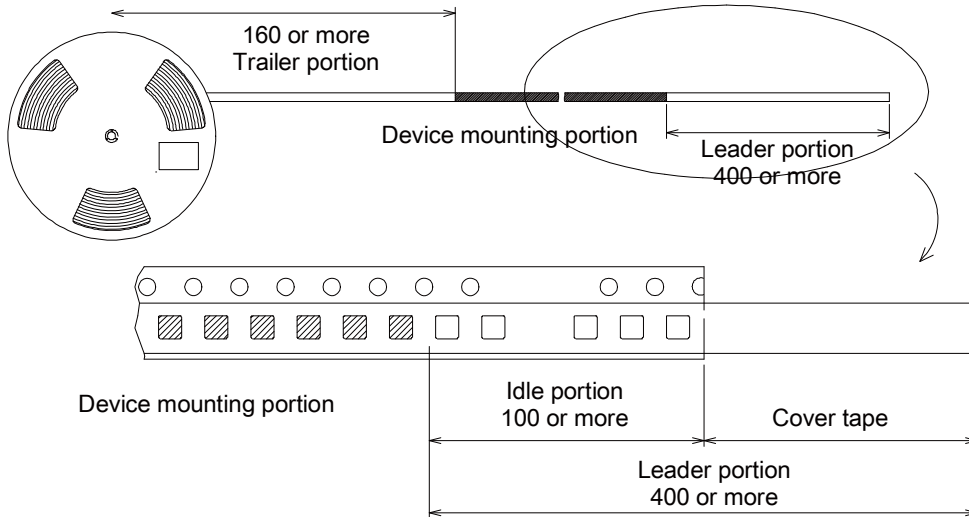
2-1. Carrier tape size (unit: mm)



2-2. Device placement direction



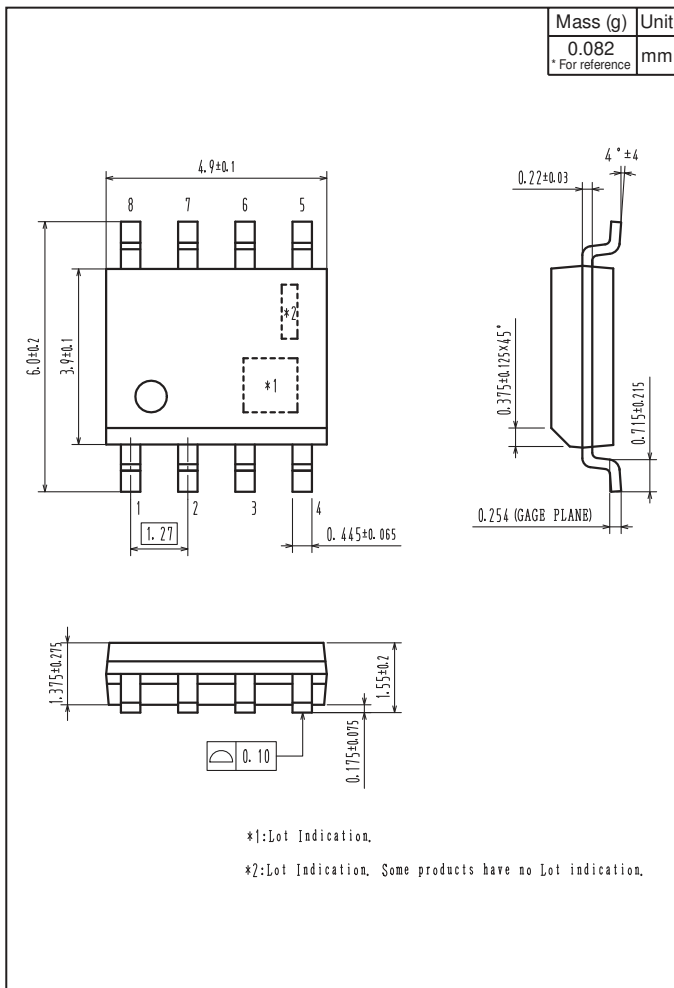
2-3. Leader portion and trailer portion (unit: mm)



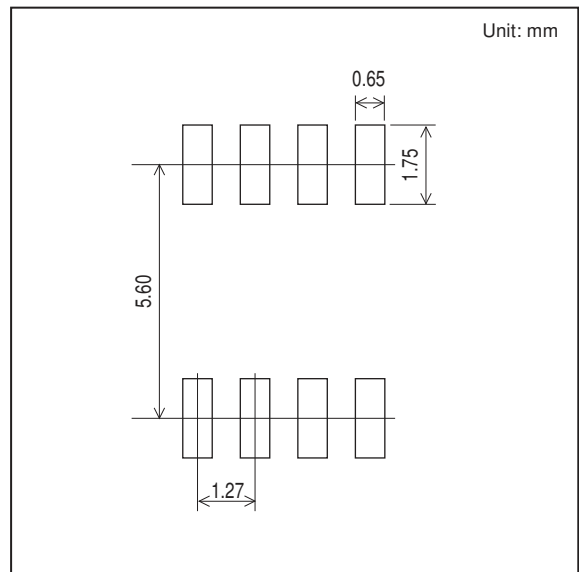
FW217A

Outline Drawing

FW217A-TL-2W



Land Pattern Example



Note on usage : Since the FW217A is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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